

Features

- Any frequency between 1 and 80 MHz accurate to 6 decimal places
- 100% pin-to-pin drop-in replacement to quartz-based oscillators
- Ultra low phase jitter: 0.5 ps (12 kHz to 20 MHz)
- Frequency stability as low as ± 10 PPM
- Industrial or extended commercial temperature range
- LVC MOS/LVTTL compatible output
- Standard 4-pin packages: 2.5 x 2.0, 3.2 x 2.5, 5.0 x 3.2, 7.0 x 5.0 mm x mm
- Outstanding silicon reliability of 2 FIT or 500 million hour MTBF
- Ultra short lead time

Applications

- SATA, SAS, Ethernet, PCI Express, video, WiFi
- Computing, storage, networking, telecom, industrial control

Electrical Characteristics^[1]

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Frequency Range						
Output Frequency Range	f	1	–	80	MHz	
Frequency Stability and Aging						
Frequency Stability	F_stab	-10	–	+10	PPM	Inclusive of Initial tolerance at 25 °C, and variations over operating temperature, rated power supply voltage and load
		-20	–	+20	PPM	
		-25	–	+25	PPM	
		-50	–	+50	PPM	
First year Aging	F_aging	-1.5	–	+1.5	PPM	25°C
10-year Aging		-5	–	+5	PPM	25°C
Operating Temperature Range						
Operating Temperature Range	T_use	-20	–	+70	°C	Extended Commercial
		-40	–	+85	°C	Industrial
Supply Voltage and Current Consumption						
Supply Voltage	Vdd	1.71	1.8	1.89	V	Supply voltages between 2.5V and 3.3V can be supported.
		2.25	2.5	2.75	V	
		2.52	2.8	3.08	V	
		2.97	3.3	3.63	V	
Current Consumption	Idd	–	31	33	mA	No load condition, f = 20 MHz, Vdd = 2.5V, 2.8V or 3.3V
		–	29	31	mA	No load condition, f = 20 MHz, Vdd = 1.8V
OE Disable Current	I_OD	–	–	31	mA	Vdd = 2.5V, 2.8V or 3.3V, OE = GND, output is Weakly Pulled Down
		–	–	30	mA	Vdd = 1.8 V. OE = GND, output is Weakly Pulled Down
Standby Current	I_std	–	–	70	μA	Vdd = 2.5V, 2.8V or 3.3V, $\overline{ST}$ = GND, output is Weakly Pulled Down
		–	–	10	μA	Vdd = 1.8 V. $\overline{ST}$ = GND, output is Weakly Pulled Down
LVCMOS Output Characteristics						
Duty Cycle	DC	45	–	55	%	
Rise/Fall Time	Tr, Tf	–	1.2	2	ns	15 pF load, 10% - 90% Vdd
Output Voltage High	VOH	90%	–	–	Vdd	IOH = -6 mA, IOL = 6 mA, (Vdd = 3.3V, 2.8V, 2.5V)
Output Voltage Low	VOL	–	–	10%	Vdd	IOH = -3 mA, IOL = 3 mA, (Vdd = 1.8V)
Input Characteristics						
Input Voltage High	VIH	70%	–	–	Vdd	Pin 1, OE or $\overline{ST}$
Input Voltage Low	VIL	–	–	30%	Vdd	Pin 1, OE or $\overline{ST}$
Input Pull-up Impedance	Z_in	–	100	250	kΩ	Pin 1, OE logic high or logic low, or $\overline{ST}$ logic high
		2	–	–	MΩ	Pin 1, $\overline{ST}$ logic low

Note:

1. All electrical specifications in the above table are specified with 15 pF output load and for all V_{dd}(s) unless otherwise stated.

Electrical Characteristics^[1] (Continued)

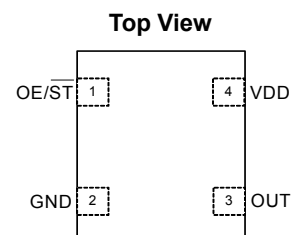
Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Startup and Resume Timing						
Startup Time	T _{start}	–	7	10	ms	Measured from the time Vdd reaches its rated minimum value
OE Enable/Disable Time	T _{oe}	–	–	150	ns	f = 80 MHz, For other frequencies, T _{oe} = 100 ns + 3 cycles
Resume Time	T _{resume}	–	6	10	ms	In standby mode, measured from the time ST pin crosses 50% threshold. Refer to Figure 5.
Jitter						
RMS Period Jitter	T _{jitt}	–	1.5	2	ps	
		–	2	3	ps	f = 75 MHz, Vdd = 1.8V
RMS Phase Jitter (random)	T _{phj}	–	0.5	1	ps	f = 10 MHz, Integration bandwidth = 12 kHz to 20 MHz

Note:

1. All electrical specifications in the above table are specified with 15 pF output load and for all Vdd(s) unless otherwise stated.

Pin Configuration

Pin	Symbol	Functionality
1	OE/ ST	Output Enable H or Open ^[2] : specified frequency output L: output is high impedance. Only output driver is disabled.
		Standby H or Open ^[2] : specified frequency output L: output is low (weak pull down). Device goes to sleep mode. Supply current reduces to I _{std} .
2	GND	Power Electrical ground ^[3]
3	OUT	Output Oscillator output
4	VDD	Power Power supply voltage ^[3]



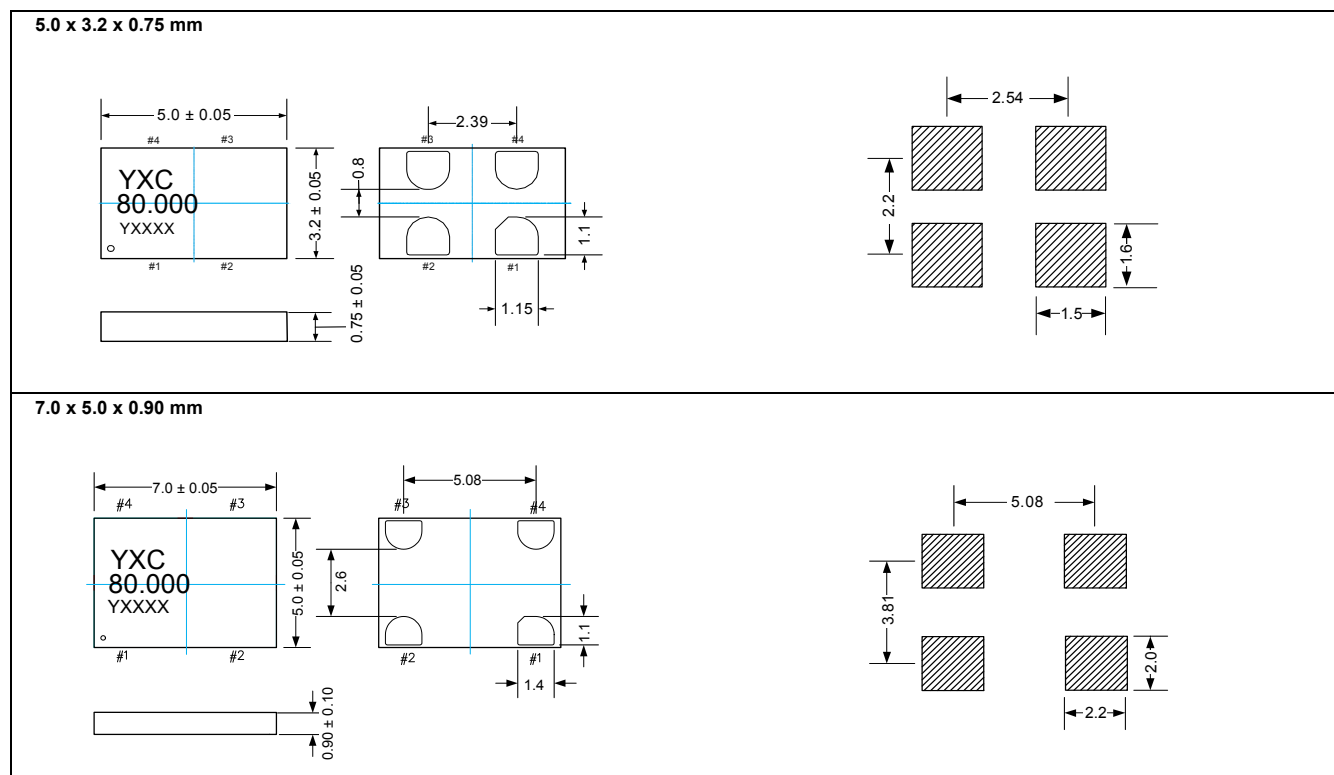
Notes:

2. A pull-up resistor of <10 kΩ between OE/ ST pin and Vdd is recommended in high noise environment.
3. A capacitor of value 0.1 μF between Vdd and GND is recommended.

Dimensions and Patterns

Package Size – Dimensions (Unit: mm) ^[4]	Recommended Land Pattern (Unit: mm) ^[5]
2.7 x 2.4 x 0.75 mm (100% compatible with 2.5 x 2.0 mm footprint)	
3.2 x 2.5 x 0.75 mm	

Dimensions and Patterns



Notes:

4. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
5. A capacitor of value 0.1 μ F between Vdd and GND is recommended.

Absolute Maximum

Attempted operation outside the absolute maximum ratings of the part may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
VDD	-0.5	4	V
Electrostatic Discharge	–	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	–	260	°C
Junction Temperature	–	150	°C

Thermal Consideration

Package	θ_{JA} , 4 Layer Board (°C/W)	θ_{JA} , 2 Layer Board (°C/W)	θ_{JC} , Bottom (°C/W)
7050	191	263	30
5032	97	199	24
3225	109	212	27
2520	117	222	26

Environmental Compliance

Parameter	Condition/Test Method
Mechanical Shock	MIL-STD-883F, Method 2002
Mechanical Vibration	MIL-STD-883F, Method 2007
Temperature Cycle	JESD22, Method A104
Solderability	MIL-STD-883F, Method 2003
Moisture Sensitivity Level	MSL1 @ 260°C

Phase Noise Plot

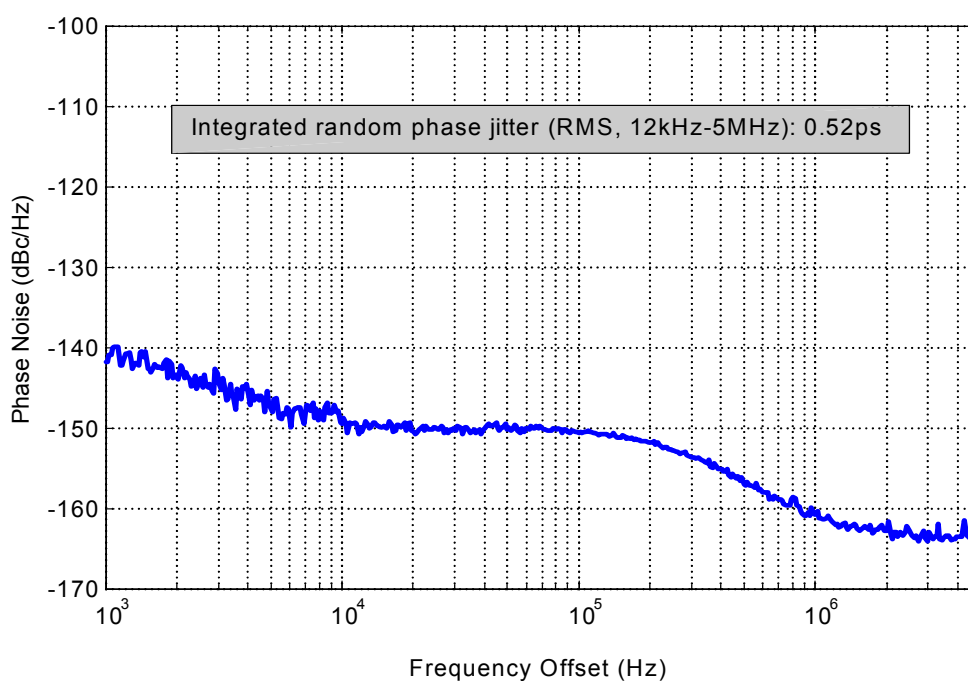


Figure 1. Phase Noise, 10 MHz, 3.3V, LVCMOS Output

Test Circuit and Waveform

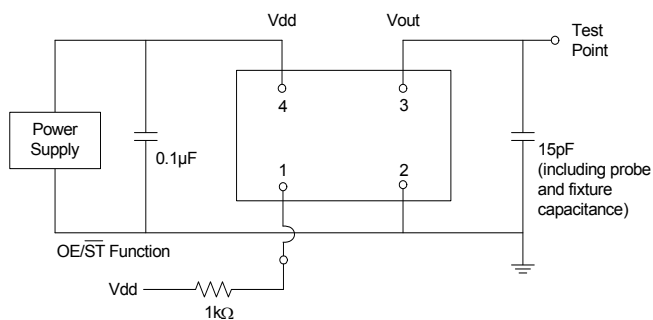


Figure 2. Test Circuit

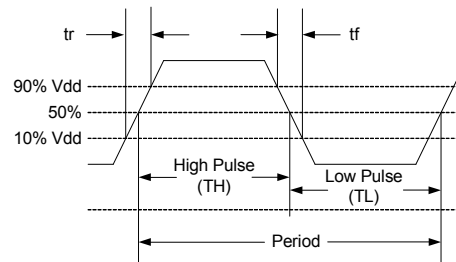


Figure 3. Waveform

Notes:

6. Duty Cycle is computed as Duty Cycle = TH/Period.

Timing Diagram

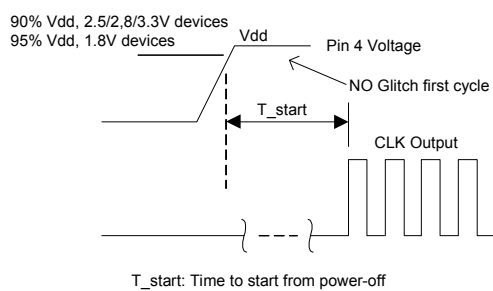


Figure 4. Startup Timing (OE/ST Mode)

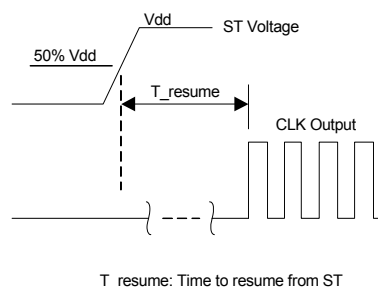


Figure 5. Standby Resume Timing (ST Mode Only)

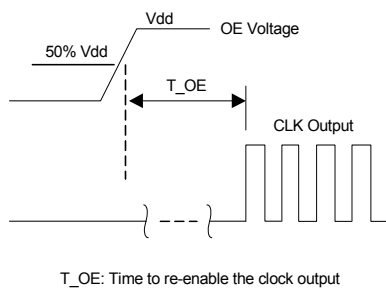


Figure 6. OE Enable Timing (OE Mode Only)

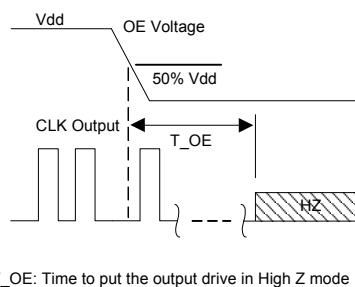


Figure 7. OE Disable Timing (OE Mode Only)

Notes:

7. YSO8208MR supports NO RUNT pulses and No glitches during startup or resume.
8. YSO8208MR supports gated output which is accurate within rated frequency stability from the first cycle.

Performance Plots

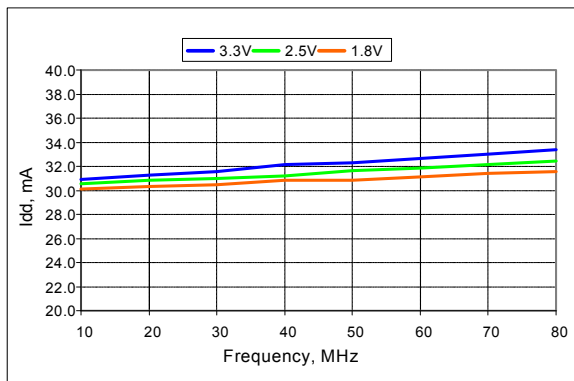


Figure 8. Idd vs Frequency

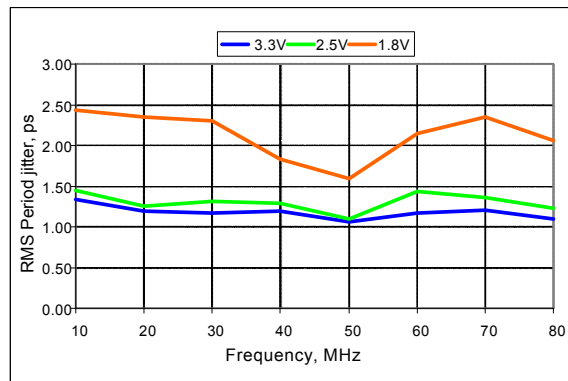


Figure 9. RMS Period Jitter vs Frequency

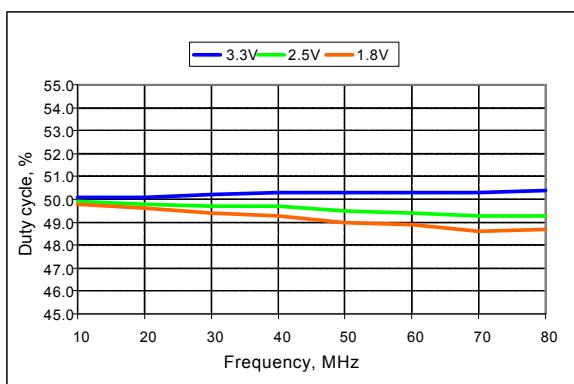


Figure 10. Duty Cycle vs Frequency

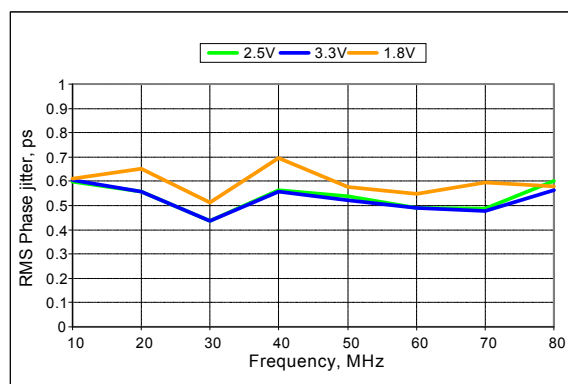


Figure 11. RMS Phase Jitter vs Frequency

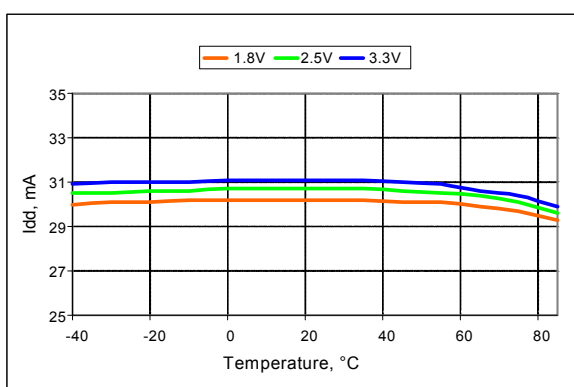


Figure 12. Idd vs Temperature, 10 MHz Output

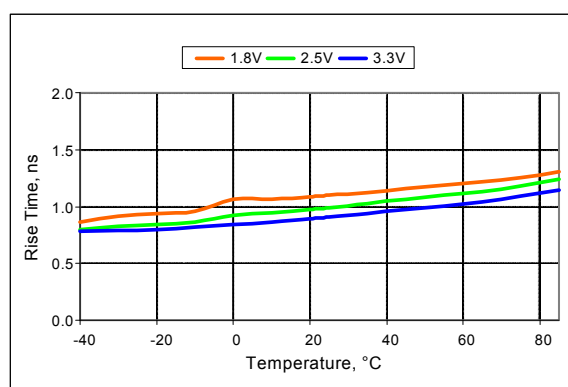


Figure 13. Rise Time vs Temperature, 75 MHz Output

Note:

9. All plots are measured with 15 pF load at room temperature, unless otherwise stated.

Programmable Drive Strength

The YSO8208MR includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining full swing with sharp edge rates.

EMI Reduction by Slowing Rise/Fall Time

Figure 14 shows the harmonic power reduction as the rise/fall times are increased (slowed down). The rise/fall times are expressed as a ratio of the clock period. For the ratio of 0.05, the signal is very close to a square wave. For the ratio of 0.45, the rise/fall times are very close to near-triangular waveform. These results, for example, show that the 11th clock harmonic can be reduced by 35 dB if the rise/fall edge is increased from 5% of the period to 45% of the period.

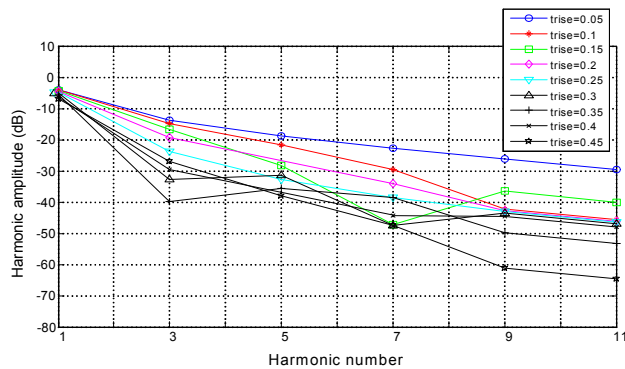


Figure 14. Harmonic EMI reduction as a Function of Slower Rise/Fall Time

Jitter Reduction with Faster Rise/Fall Time

Power supply noise can be a source of jitter for the downstream chipset. One way to reduce this jitter is to increase rise/fall time (edge rate) of the input clock. Some chipsets would require faster rise/fall time in order to reduce their sensitivity to this type of jitter. The YSO8208MR provides up to 3 additional high drive strength settings for very fast rise/fall time. Refer to the [Rise/Fall Time Tables](#) to determine the proper drive strength.

High Output Load Capability

The rise/fall time of the input clock varies as a function of the actual capacitive load the clock drives. At any given drive strength, the rise/fall time becomes slower as the output load increases. As an example, for a 3.3V YSO8208MR device with default drive strength setting, the typical rise/fall time is 1.15ns for 15 pF output load. The typical rise/fall time slows down to 2.72ns when the output load increases to 45 pF.

One can choose to speed up the rise/fall time to 1.41ns by then increasing the drive strength setting on the YSO8208MR. The YSO8208MR can support up to 60 pF or higher in maximum capacitive loads with up to 3 additional drive strength settings. Refer to the [Rise/Fall Time Tables](#) to determine the proper drive strength for the desired combination of output load vs. rise/fall time

YSO8208MR Drive Strength Selection

Tables 1 through 5 define the rise/fall time for a given capacitive load and supply voltage.

1. Select the table that matches the YSO8208MR nominal supply voltage (1.8V, 2.5V, 2.8V, 3.0V, 3.3V).
2. Select the capacitive load column that matches the application requirement (5 pF to 60 pF)
3. Under the capacitive load column, select the desired rise/fall times.
4. The left-most column represents the part number code for the corresponding drive strength.
5. Add the drive strength code to the part number for ordering purposes.

Rise/Fall Time (10% to 90%) vs C_{LOAD} Tables

Rise/Fall Time Typ (ns)					
Drive Strength \ C_{LOAD}	5 pF	15 pF	30 pF	45 pF	60 pF
L	12.45	17.68	19.48	46.21	57.82
A	6.50	10.27	16.21	23.92	30.73
R	4.38	7.05	11.61	16.17	20.83
B	3.27	5.30	8.89	12.18	15.75
S	2.62	4.25	7.20	9.81	12.65
D	2.19	3.52	6.00	8.31	10.59
T	1.76	3.01	5.14	7.10	9.15
E	1.59	2.59	4.49	6.25	7.98
U	1.49	2.28	3.96	5.55	7.15
F	1.22	2.10	3.57	5.00	6.46
W	1.07	1.88	3.23	4.50	5.87
G	1.01	1.64	2.95	4.12	5.40
X	0.96	1.50	2.74	3.80	4.98
K	0.92	1.41	2.56	3.52	4.64
Y	0.88	1.34	2.39	3.25	4.32
Q	0.86	1.29	2.24	3.04	4.06
Z or "": Default	0.82	1.24	2.07	2.89	3.82
M	0.77	1.20	1.94	2.72	3.61
N	0.66	1.15	1.84	2.58	3.41
P	0.51	1.09	1.76	2.45	3.24

Table 1. Vdd = 1.8V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)					
Drive Strength \ C_{LOAD}	5 pF	15 pF	30 pF	45 pF	60 pF
L	8.68	13.59	18.36	32.70	42.06
A	4.42	7.18	11.93	16.60	21.38
R	2.93	4.78	8.15	11.19	14.59
B	2.21	3.57	6.19	8.55	11.04
S	1.67	2.87	4.94	6.85	8.80
D	1.50	2.33	4.11	5.68	7.33
T	1.06	2.04	3.50	4.84	6.26
E	0.98	1.69	3.03	4.20	5.51
U	0.93	1.48	2.69	3.73	4.92
F	0.90	1.37	2.44	3.34	4.42
W	0.87	1.29	2.21	3.04	4.02
G or "": Default	0.67	1.20	2.00	2.79	3.69
X	0.44	1.10	1.86	2.56	3.43
K	0.38	0.99	1.76	2.37	3.18
Y	0.36	0.83	1.66	2.20	2.98
Q	0.34	0.71	1.58	2.07	2.80
Z	0.33	0.65	1.51	1.95	2.65
M	0.32	0.62	1.44	1.85	2.50
N	0.31	0.59	1.37	1.77	2.39
P	0.30	0.57	1.29	1.70	2.28

Table 2. Vdd = 2.5V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)					
Drive Strength \ C_{LOAD}	5 pF	15 pF	30 pF	45 pF	60 pF
L	7.93	12.69	17.94	30.10	38.89
A	4.06	6.66	11.04	15.31	19.80
R	2.68	4.40	7.53	10.29	13.37
B	2.00	3.25	5.66	7.84	10.11
S	1.59	2.57	4.54	6.27	8.07
D	1.19	2.14	3.76	5.21	6.72
T	1.00	1.79	3.20	4.43	5.77
E	0.94	1.51	2.78	3.84	5.06
U	0.90	1.38	2.48	3.40	4.50
F	0.87	1.29	2.21	3.03	4.05
W	0.62	1.19	1.99	2.76	3.68
G or "": Default	0.41	1.08	1.84	2.52	3.36
X	0.37	0.96	1.72	2.33	3.15
K	0.35	0.78	1.63	2.15	2.92
Y	0.33	0.67	1.54	2.00	2.75
Q	0.32	0.63	1.46	1.89	2.57
Z	0.31	0.60	1.39	1.80	2.43
M	0.30	0.57	1.31	1.72	2.30
N	0.30	0.56	1.22	1.63	2.22
P	0.29	0.54	1.13	1.55	2.13

Table 3. Vdd = 2.8V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)					
Drive Strength \ C_{LOAD}	5 pF	15 pF	30 pF	45 pF	60 pF
L	7.18	11.59	17.24	27.57	35.57
A	3.61	6.02	10.19	13.98	18.10
R	2.31	3.95	6.88	9.42	12.24
B	1.65	2.92	5.12	7.10	9.17
S	1.43	2.26	4.09	5.66	7.34
D	1.01	1.91	3.38	4.69	6.14
T	0.94	1.51	2.86	3.97	5.25
E	0.90	1.36	2.50	3.46	4.58
U	0.86	1.25	2.21	3.03	4.07
F or "": Default	0.48	1.15	1.95	2.72	3.65
W	0.38	1.04	1.77	2.47	3.31
G	0.36	0.87	1.66	2.23	3.03
X	0.34	0.70	1.56	2.04	2.80
K	0.33	0.63	1.48	1.89	2.61
Y	0.32	0.60	1.40	1.79	2.43
Q	0.32	0.58	1.31	1.69	2.28
Z	0.30	0.56	1.22	1.62	2.17
M	0.30	0.55	1.12	1.54	2.07
N	0.30	0.54	1.02	1.47	1.97
P	0.29	0.52	0.95	1.41	1.90

Table 4. Vdd = 3.3V Rise/Fall Times for Specific C_{LOAD}